

Features

- 260W peak pulse power ($T_P=8/20\mu s$)
- Bidirectional configuration
- Protects one I/O port
- Low clamping voltage
- Low Leakage current
- ESD-immunity acc. IEC 61000-4-2 $\pm 20KV$ contact $\pm 20KV$ air
- IEC 61000-4-4 (EFT) 40A (5/50ns)



DFN1006



Schematic Diagram

Applications

- Cell Phone
- PDA
- Notebook
- Digital Cameras
- Portable Instrumentation
- Audio and video equipment

Absolute Maximum Ratings ($T_A=25^\circ C$, unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power ($T_P=8/20\mu S$)	P_{PP}	260	W
Peak Pulse Current ($T_P=8/20\mu S$)	I_{PP}	6	A
Junction Temperature	T_J	-55 To +125	$^\circ C$
Storage Temperature	T_{STG}	-55 To +150	$^\circ C$

Electrical Characteristics ($T_A=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Reverse Stand-Off Voltage	V_{RWM}	-	-	-	24	V
Reverse Breakdown Voltage	V_{BR}	$I_T=1mA$	26.7	-	-	V
Reverse Leakage Current	I_R	$V_R=24V$	-	0.1	0.5	μA
Clamping Voltage	V_C	$I_{PP}=6A, T_P=8/20\mu S$	-	-	44	V
Junction Capacitance	C_J	$V_R=0V, f=1MHz$	-	15	20	pF

Typical Characteristic Curves

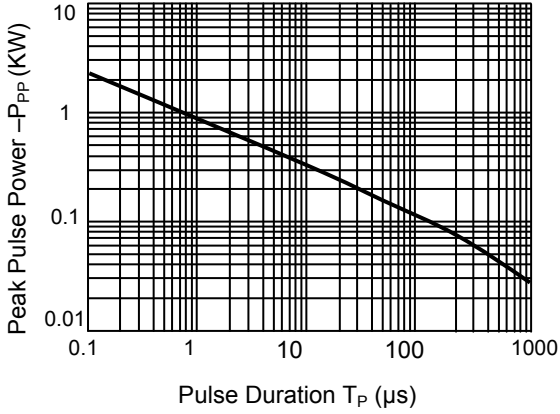


Figure 1. Peak Pulse Power Rating Curve

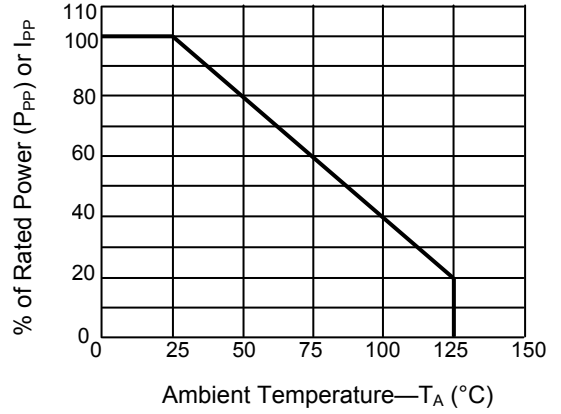


Figure 2. Pulse Derating Curve

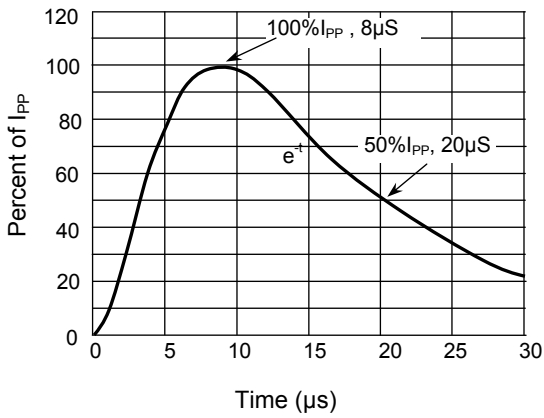


Figure 3. Pulse Waveform - 8/20 μs

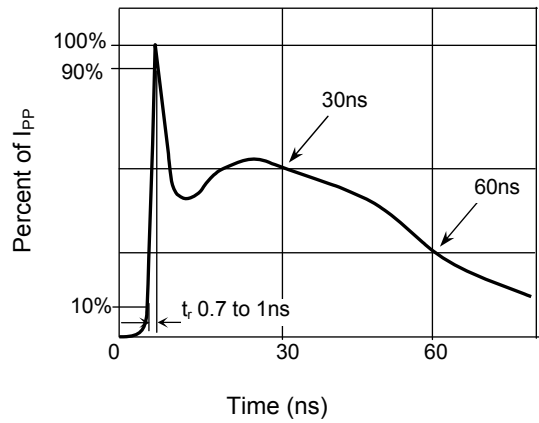
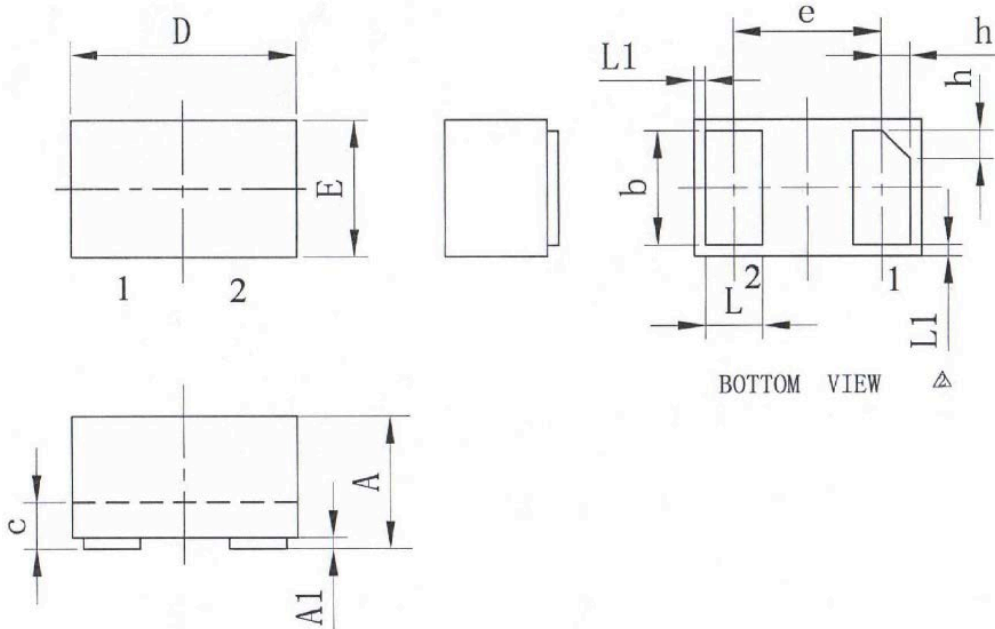


Figure 4. Pulse Waveform - ESD (IEC61000-4-2)

Product Dimensions DFN1006



Symbol	Dimensions in Millimeters		
	Min	Nom	Max
A	0.45	0.50	0.55
A1	0.00	0.02	0.05
b	0.45	0.50	0.55
c	0.12	0.15	0.18
D	0.95	1.00	1.05
e	0.650 BSC		
E	0.55	0.60	0.65
L	0.20	0.25	0.30
L1	0.050 REF		
h	0.07	0.12	0.17
Carrier Dimensions	20x20		

Order Information

Device	Package	Marking	Carrier	Quantity	HSF Status
GSEZ24B150	DFN1006	CB	Tape & Reel	10,000pcs / Reel	RoHS Compliant